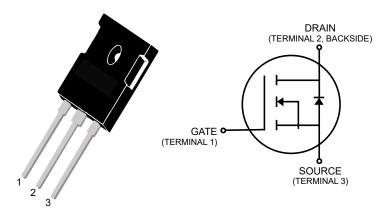
# 1200V, 80 mΩ N-Channel mSiC™ MOSFET

MSC080SMA120B



### **Product Overview**

1200V, 80 m $\Omega$  typical at V<sub>GS</sub> = 20V, 90 m $\Omega$  typical at V<sub>GS</sub> = 18V, Silicon Carbide (SiC) N-Channel MOSFET, TO-247.



#### **Features**

- AEC-Q101 qualified option available
- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature,  $T_{I(max)} = 175 \, ^{\circ}\text{C}$
- · Fast and reliable body diode
- Superior avalanche ruggedness
- · RoHS compliant

#### **Benefits**

- High efficiency to enable lighter and more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- · Eliminates the need for external freewheeling diode
- · Lower system cost of ownership

### **Applications**

- Photovoltaic (PV) inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- · Hybrid Electric Vehicle (HEV) powertrain and Electric Vehicle (EV) charger
- Power supply and distribution

# 1. Device Specifications

This section shows the specifications of this device.

### 1.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings of this device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain source voltage	1200	V
I <sub>D</sub>	Continuous drain current at T <sub>C</sub> = 25 °C	40	Α
	Continuous drain current at T <sub>C</sub> = 100 °C	28	
I <sub>DM</sub>	Pulsed drain current <sup>1</sup>	111	
$V_{GS}$	Gate-source voltage	23 to -10	V
	Transient gate-source voltage	25 to -12	
P <sub>D</sub>	Total power dissipation at T <sub>C</sub> = 25 °C	231	W
	Linear derating factor	1.5	W/°C

#### Note:

1. Repetitive rating: pulse width and case temperature are limited by the maximum junction temperature.

The following table shows the thermal and mechanical characteristics of this device.

Table 1-2. Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min.	Тур.	Max.	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance	_	0.5	0.65	°C/W
Tj	Operating junction temperature	-55	_	175	°C
T <sub>STG</sub>	Storage temperature	-55	_	175	
TL	Lead temperature for 10 seconds	_	_	300	°C
$\tau_{M}$	Mounting torque, M3 screw for heat sink attachment (requires 1, not included)	_	0.8	_	N·m
Wt	Package weight	_	6.2	_	g

ESD practices should comply with JESD-625.

### 1.2 Electrical Performance

The following table shows the static characteristics of this device.  $T_J$  = 25 °C unless otherwise specified.

Table 1-3. Static Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$V_{GS} = 0V, I_D = 100 \mu A$	1200	_	_	V
R <sub>DS(on)</sub>	Drain-source on resistance <sup>1</sup>	V <sub>GS</sub> = 20V, I <sub>D</sub> = 15A	_	80	100	mΩ
		V <sub>GS</sub> = 18V, I <sub>D</sub> = 15A	_	90	_	
V <sub>GS(th)</sub>	Gate-source threshold voltage	$V_{GS} = V_{DS}$ , $I_D = 1 \text{ mA}$	1.9	3.0	5.0	V
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>DS</sub> = 1200V, V <sub>GS</sub> = 0V	_	0.2	30	μΑ
		V <sub>DS</sub> = 1200V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 175 °C	_	2	_	
I <sub>GSS</sub>	Gate-source leakage current	V <sub>GS</sub> = 20V/–10V	_	_	±100	nA

#### Note:

1. Pulse test: pulse width < 380  $\mu$ s, duty cycle < 2%.

The following table shows the dynamic characteristics of this device.  $T_J$  = 25 °C unless otherwise specified. The dynamic characteristics are characterized, not 100% tested, at the recommended operating  $V_{GS}$  = 20V/–5V.

**Table 1-4.** Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
C <sub>iss</sub>	Input capacitance	$V_{GS} = 0V$	_	1031	_	pF
C <sub>rss</sub>	Reverse transfer capacitance	V <sub>DD</sub> = 1000V	_	6	_	
C <sub>oss</sub>	Output capacitance	$V_{AC} = 25 \text{ mV}$ f = 200 kHz	_	92	_	
$Q_{G}$	Total gate charge	V <sub>GS</sub> = -5V/20V	_	64	<u> </u>	nC
Q <sub>GS</sub>	Gate-source charge	V <sub>DD</sub> = 800V	_	12	<u> </u>	
$Q_{GD}$	Gate-drain charge	I <sub>D</sub> = 15A	_	19	_	
t <sub>d(on)</sub>	Turn-on delay time	V <sub>DD</sub> = 850V	_	21	<u> </u>	ns
t <sub>r</sub>	Voltage rise time	$V_{GS} = -5V/20V$	_	10	<u> </u>	
t <sub>d(off)</sub>	Turn-off delay time	I <sub>D</sub> = 20A	_	19	<b> </b> -	
t <sub>f</sub>	Voltage fall time	$R_{G(ext)} = 4\Omega$	_	16	_	
E <sub>on</sub>	Turn-on switching energy	Freewheeling diode = MSC080SMA120B (V <sub>GS</sub> = -5V);	_	360	<b> </b> -	μJ
E <sub>off</sub>	Turn-off switching energy	reference Figure 1-19	_	65	_	
ESR	Gate equivalent series resistance	f = 1 MHz, 25 mV, drain short	_	1.9	_	Ω
SCWT	Short circuit withstand time	$V_{DS} = 960V, V_{GS} = 20V$	_	3.0	_	μs
E <sub>AS</sub>	Avalanche energy, single pulse	I <sub>D</sub> = 15A	_	1300	_	mJ

The following table shows the body diode characteristics of this device.  $T_J = 25$  °C unless otherwise specified. The body diode reverse recovery is characterized, not 100% tested.

Table 1-5. Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
$V_{SD}$	Diode forward voltage	I <sub>SD</sub> = 15A, V <sub>GS</sub> = 0V	_	3.7	_	V
		$I_{SD} = 15A, V_{GS} = -5V$	_	3.9	5.0	
t <sub>rr</sub>	Reverse recovery time	$I_{SD}$ = 20A, $V_{GS}$ = –5V, Drive $R_G$ = $4\Omega$ , $V_{DD}$ =	_	28	_	ns
Q <sub>rr</sub>	Reverse recovery charge	800V, dI/dt = -5100 A/μs	_	367	_	nC
I <sub>RRM</sub>	Reverse recovery current		_	12	_	Α

## 1.3 Typical Performance Curves

Data for performance curves are characterized, not 100% tested.

Figure 1-1. Drain Current vs.  $V_{DS}$  at  $T_{J}$ 

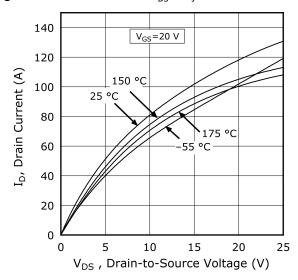


Figure 1-2. Drain Current vs.  $V_{DS}$  at  $V_{GS}$ 

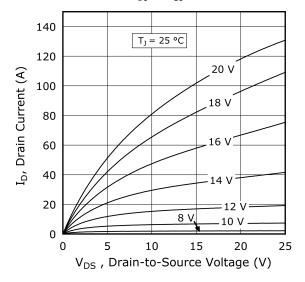


Figure 1-3. Drain Current vs.  $V_{DS}$  at  $V_{GS}$ 

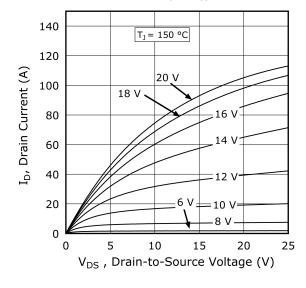


Figure 1-4. Drain Current vs.  $V_{DS}$  at  $V_{GS}$ 

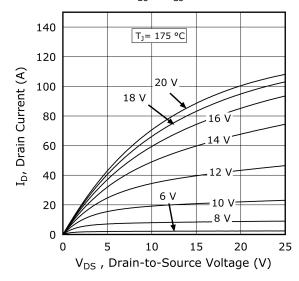


Figure 1-5. R<sub>DS(on)</sub> vs. Junction Temperature

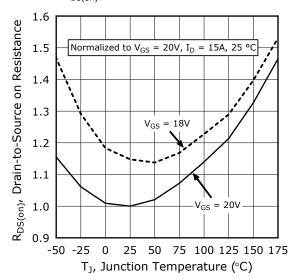


Figure 1-6. Gate Charge Characteristics

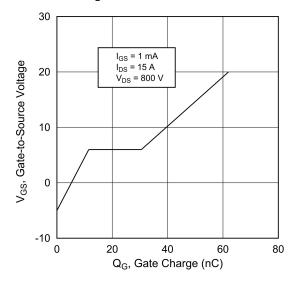


Figure 1-7. Capacitance vs. Drain-to-Source Voltage

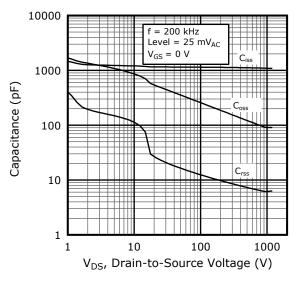


Figure 1-8. Output Charge vs. Drain-to-Source Voltage

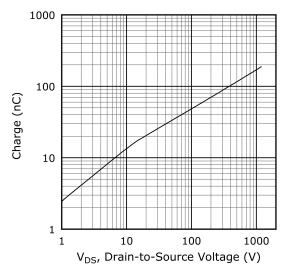


Figure 1-9. Output Stored Energy vs. V<sub>DS</sub>

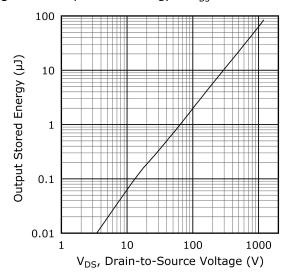


Figure 1-10.  $I_D$  vs.  $V_{DS}$   $3^{rd}$  Quadrant Conduction

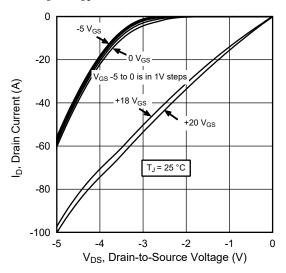


Figure 1-11.  $I_D$  vs.  $V_{DS}$   $3^{rd}$  Quadrant Conduction

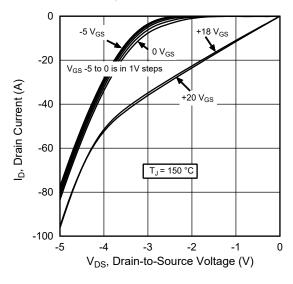


Figure 1-12. Switching Energy  $E_{on}$  vs.  $V_{DS} \& I_{D}$ 

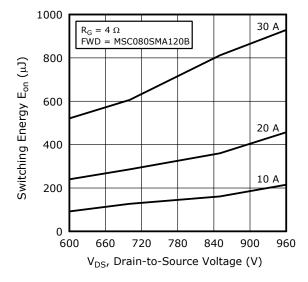


Figure 1-13. Switching Energy  $E_{off}$  vs.  $V_{DS} \& I_{D}$ 

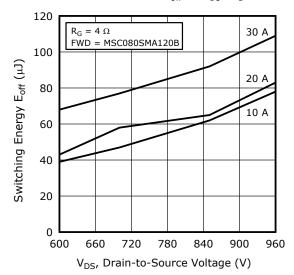


Figure 1-14. Switching Energy vs. R<sub>G</sub>

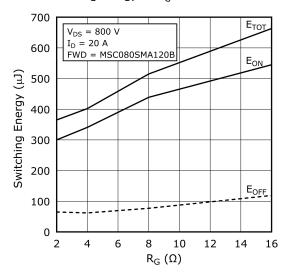


Figure 1-15. Switching Energy vs. Junction Temperature

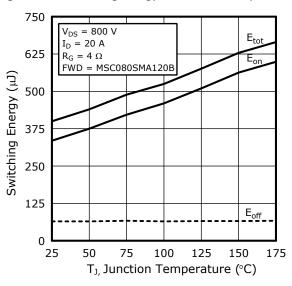


Figure 1-16. Threshold Voltage vs. Junction Temperature

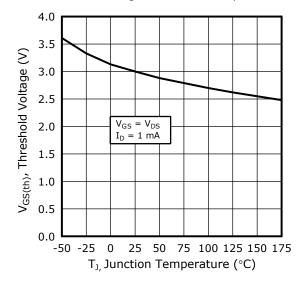


Figure 1-17. Forward Safe Operating Area

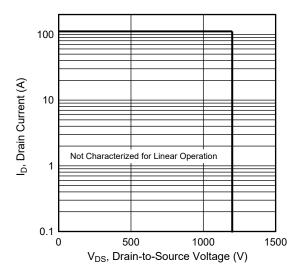
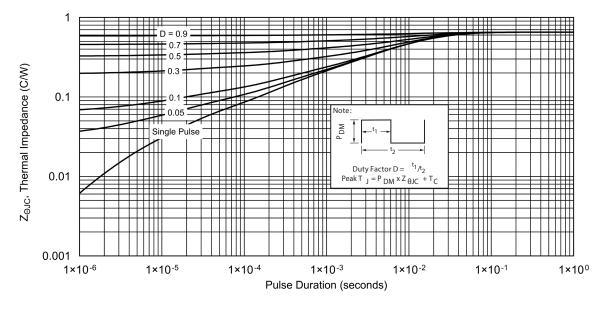
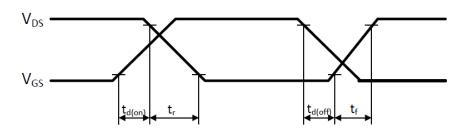


Figure 1-18. Maximum Transient Thermal Impedance



The following figure shows the switching waveform diagram of this device.

Figure 1-19. Switching Waveform



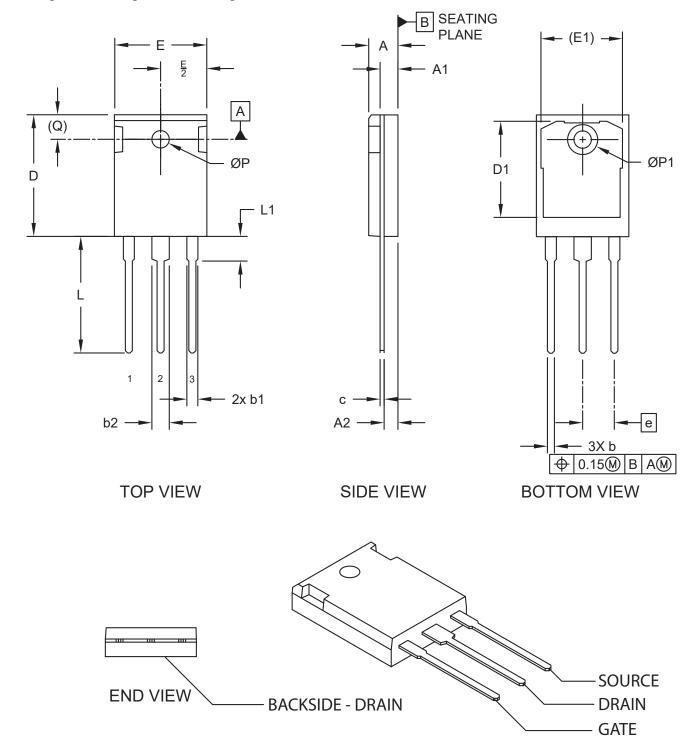
# 2. Package Specification

This section shows the package specification of this device.

# 2.1 Package Outline Drawing

The following figure illustrates the TO-247 package outline of this device.

Figure 2-1. Package Outline Drawing



The following table shows the TO-247 dimensions and should be used in conjunction with the package outline drawing.

Table 2-1. TO-247 Dimensions

Symbol	Description	Min. (mm)	Max. (mm)
N	Number of leads	3	·
е	Pitch	5.44 BSC	
Α	Overall height	4.70	5.31
A1	Tab height	1.50	2.49
A2	Seating plane to lead	2.21	2.59
b	Lead width	1.02	1.40
b1	Lead shoulder width (X2)	1.65	2.41
b2	Lead shoulder width	2.87	3.38
С	Lead thickness	0.41	0.79
L	Lead length	19.81	20.32
L1	Lead shoulder length	3.99	4.50
D	Molded body length	20.80	21.46
D1	Thermal pad length	16.25	17.65
E	Total width	15.49	16.26
E1	Thermal pad width	13.10	14.50
Q	Hole center to tab edge	6.15 REF	
ØP	Hole diameter	3.51	3.81
ØP1	Thermal pad hole diameter	7.18 REF	

#### **Notes:**

Dimensioning and tolerancing per ASME Y14.5M.

- BSC: Basic dimension. Theoretically exact value shown without tolerances.
- REF: Reference dimension, usually without tolerance, for information purposes only.

# 3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Table 3-1. Revision History

Revision	Date	Description
D	07/2024	Added $\tau_M$ symbol for mounting torque in Table 1-2
С	05/2024	The following changes are made in this revision of the document:
		Added Figure 1-9.
В	08/2023	The following changes are made in this revision of the document:
		<ul> <li>Updated typical value for zero gate voltage drain current in Table 1-3.</li> </ul>
		<ul> <li>Updated typical values for diode forward voltage in Table 1-5.</li> </ul>
		• Updated Figure 1-7.
A	08/2022	Document migrated from Microsemi template to Microchip template; Assigned Microchip literature number DS-00004672A, which replaces the previous Microsemi literature number 050-7736.
Initial release (Microsemi Revision A)	11/2019	Document created.

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